

isc Silicon NPN Power Transistor

2SD424

DESCRIPTION

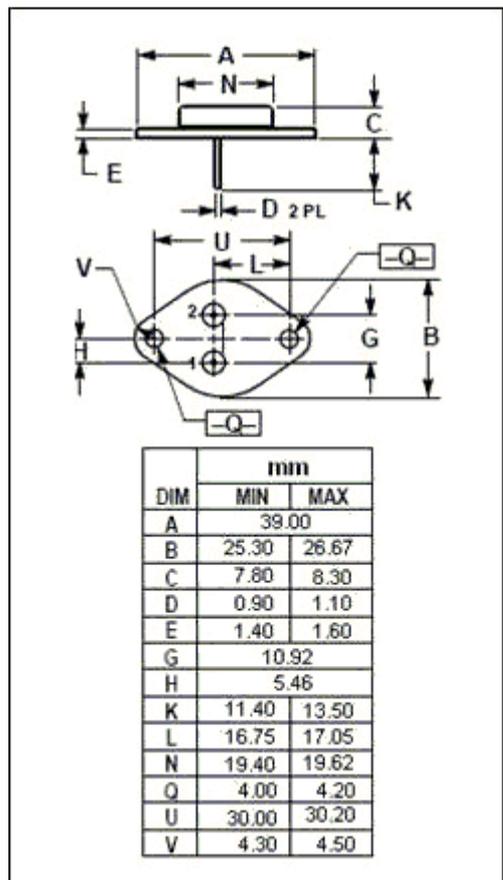
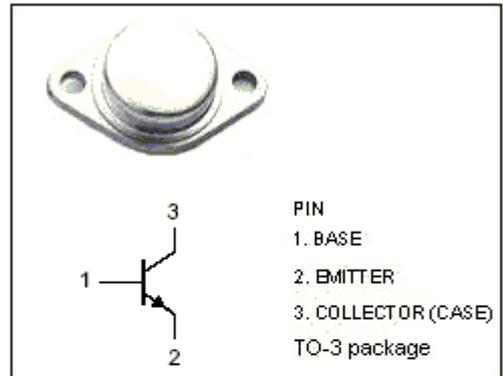
- High Power Dissipation-
: $P_C = 150W @ T_C = 25^\circ C$
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 180V(\text{Min})$
- Complement to Type 2SB554

APPLICATIONS

- Designed for power amplifier ,DC-DC converter and regulator applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	180	V
V_{CEO}	Collector-Emitter Voltage	180	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	15	A
I_B	Base Current-Continuous	1.5	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	150	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$



isc Silicon NPN Power Transistor**2SD424****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=0.1\text{A}; I_B=0$	180			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=10\text{mA}; I_C=0$	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=10\text{A}; I_B=1\text{A}$			3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=10\text{A}; V_{CE}=5\text{V}$			2.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=90\text{V}; I_E=0$			0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			0.1	mA
h_{FE}	DC Current Gain	$I_C=2\text{A}; V_{CE}=5\text{V}$	40		140	
f_T	Current-Gain—Bandwidth Product	$I_C=2\text{A}; V_{CE}=5\text{V}$		5		MHz
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f=1\text{MHz}$		300		pF

◆ **h_{FE-2} Classifications**

R	O
40-80	70-140